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|  | <h2>SI7898DP-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SI7898DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 150V 3A PPAK SO-8</p> <p>Datenblätter:  SI7898DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 2879 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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| Teilenummer | SI7898DP-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CH 150V 3A PPAK SO-8 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 2879 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | PowerPAK® SO-8 |
| Supplier Device-Gehäuse | PowerPAK® SO-8 |
| Verlustleistung (max) | 1.9W (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 150V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 3A (Ta) |
| Rds On (Max) @ Id, Vgs | 85 mOhm @ 3.5A, 10V |
| VGS (th) (Max) @ Id | 4V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 21nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | - |
| Antriebsspannung (Max Rds On, Min Rds On) | 6V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |

































SI7898DP-T1-GE3 ist neu im Original, Suche SI7898DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7898DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7898DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|---|
|  SI7900AEDA-T1-E3 VISHAY VISHAY VSSOP-8 |  SI7900ADN SI SI7900ADN SI |  SI7900AEDN-T1 VISHAY SI7900AEDN-T1 VISHAY |  SI7898DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 3A PPAK SO-8 |
|  SI7898DP-T1-E3. VISHAY VISHAY QFN8 |  SI7898DP-T1 VIHS SI7898DP-T1 VIHS |  SI7898DP SI SI7898DP SI |  SI7898DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 3A PPAK SO-8 |

heiße Teile

Mehr

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|  SI7886ADP-T1-GE3 |  SI7886ADP-T1-GE3 |  SI7886DP |  SI7886DP-T1 |  SI7886DP-T1-E3 |
|  SI7886DP-T1-GE3 |  SI7888DP-T1-E3 |  SI7888DP-T1-E3 |  SI7888DP-T1-GE3 |  SI7888DP-T1-E3 |
|  SI7892ADP-T1-E3 |  SI7892ADP-T1-GE3 |  SI7892ADP-T1-GE3. |  SI7892BDP-T1-E3 |  SI7892BDP-T1-E3 |
|  SI7892BDP-T1-GE3 |  SI7892BDP-T1-GE3 |  SI7892DP |  SI7892DP-T1 |  SI7892DP-T1-E3 |
|  SI7892DP-T1-GE3 |  SI7898DP |  SI7898DP-T1-E3 |  SI7898DP-T1-E3 |  SI7898DP-T1-GE3 |
|  SI7900ADN |  SI7900AEDN |  SI7900AEDN-T1 |  SI7900AEDN-T1-E3 |  SI7900AEDN-T1-E3 |
|  SI7900AEDN-T1-GE3 |  SI7900AEDN-T1-GE3 |  SI7900EDN |  SI7900EDN-T1 |  SI7900EDN-T1-E3 |
|  SI7900EDN-T1-GE3 |  SI7901EDN-T1 |  SI7901EDN-T1-E3 |  SI7901EDN-T1-E3 |  SI7904BDN-T1-E3 |
|  SI7904BDN-T1-E3 |  SI7904BDN-T1-GE3 |  SI7904BDN-T1-GE3 |  SI7904DN |  SI7904DN-T1 |
|  SI7904DN-T1-E3 |  SI7904DN-T1-E3 |  SI7904DN-T1-GE3 |  SI7904DN-T1-GE3 |  SI7905DN-T1-GE3 |

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